

SN74ALS234

64 × 4 ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY

SDAS106B – OCTOBER 1986 – REVISED SEPTEMBER 1993

- Asynchronous Operation
- Organized as 64 Words by 4 Bits
- Data Rates From 0 to 30 MHz
- 3-State Outputs
- Package Options Include Plastic Small-Outline Packages (DW), Plastic J-Leaded Chip Carriers (FN), and Standard Plastic 300-mil DIPs (N)

description

The SN74ALS234 is a 256-bit memory utilizing advanced low-power Schottky IMPACT™ technology. It features high speed with fast fall-through times and is organized as 64 words by 4 bits.

A first-in, first-out (FIFO) memory is a storage device that allows data to be written into and read from its array at independent data rates. The SN74ALS234 is designed to process data at rates from 0 to 30 MHz in a bit-parallel format, word by word.

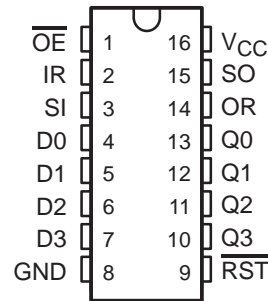
Data is written into memory on the rising edge of the shift-in (SI) input. When SI goes low, the first data word ripples through to the output (see Figure 1). As the FIFO fills up, the data words stack up in the order they were written. When the FIFO is full, additional shift-in pulses have no effect. Data is shifted out of memory on the falling edge of the shift-out (SO) input (see Figure 2). When the FIFO is empty, additional SO pulses have no effect. The last data word remains at the outputs until a new word falls through or reset ($\overline{\text{RST}}$) goes low.

Status of the SN74ALS234 FIFO memory is monitored by the output-ready (OR) and input-ready (IR) flags. When OR is high, valid data is available at the outputs. OR is low when SO is high and stays low when the FIFO is empty. IR is high when the inputs are ready to receive more data. IR is low when SI is high and stays low when the FIFO is full.

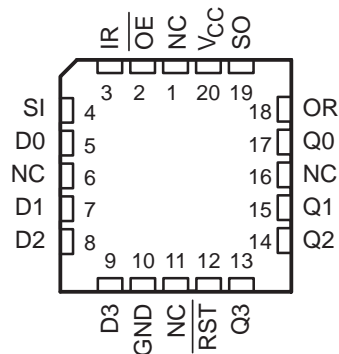
When the FIFO is empty, input data is shifted to the output automatically when SI goes low. If SO is held high during this time, the OR flag pulses high indicating valid data at the outputs (see Figure 3).

When the FIFO is full, data can be shifted in automatically by holding SI high and taking SO low. One propagation delay after SO goes low, IR will go high. If SI is still high when IR goes high, data at the inputs are automatically shifted in. Since IR is normally low when the FIFO is full and SI is high, only a high-level pulse is seen on the IR output (see Figure 4).

DW OR N PACKAGE
(TOP VIEW)



FN PACKAGE
(TOP VIEW)



NC – No internal connection



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

IMPACT is a trademark of Texas Instruments Incorporated.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

Copyright © 1993, Texas Instruments Incorporated

SN74ALS234

64 × 4 ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY

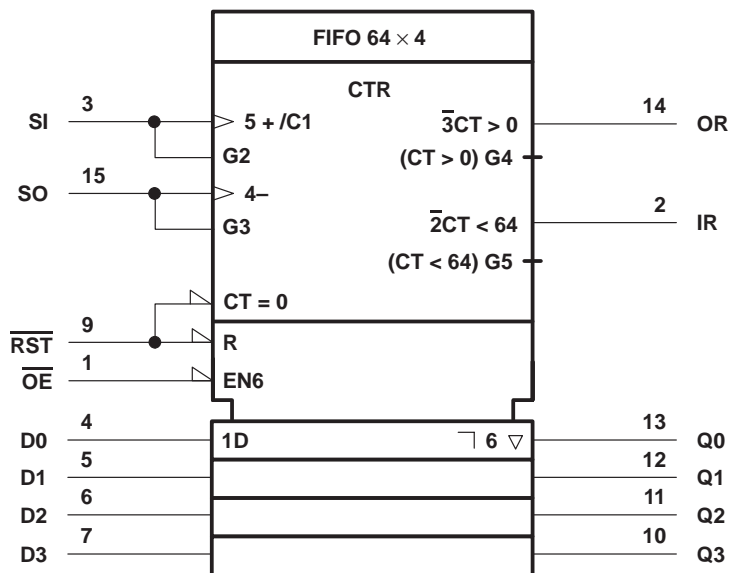
SDAS106B – OCTOBER 1986 – REVISED SEPTEMBER 1993

description (continued)

The FIFO must be reset after power up with a low-level pulse on the master reset (\overline{RST}) input. This sets IR high and OR low signifying that the FIFO is empty. Resetting the FIFO sets the outputs to a low logic level (see Figure 1). If SI is high when \overline{RST} goes high, the input data is shifted in and IR goes low and remains low until SI goes low. If SI goes low before \overline{RST} goes high, the input data will not be shifted in and IR goes high. Data outputs are noninverting with respect to the data inputs and are at high impedance when the output-enable (\overline{OE}) input is high. \overline{OE} does not affect the IR or OR.

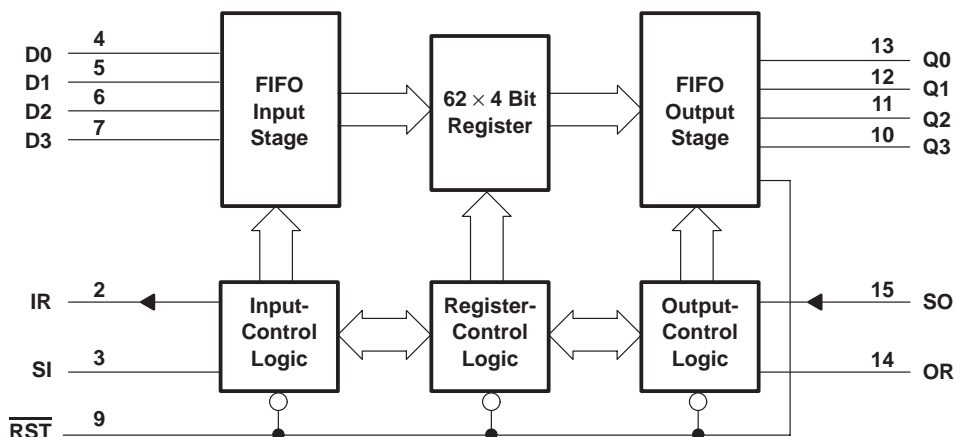
The SN74ALS234 is characterized for operation from 0°C to 70°C.

logic symbol†



† This symbol is in accordance with ANSI/IEEE Standard 91-1984 and IEC Publication 617-12.

functional block diagram

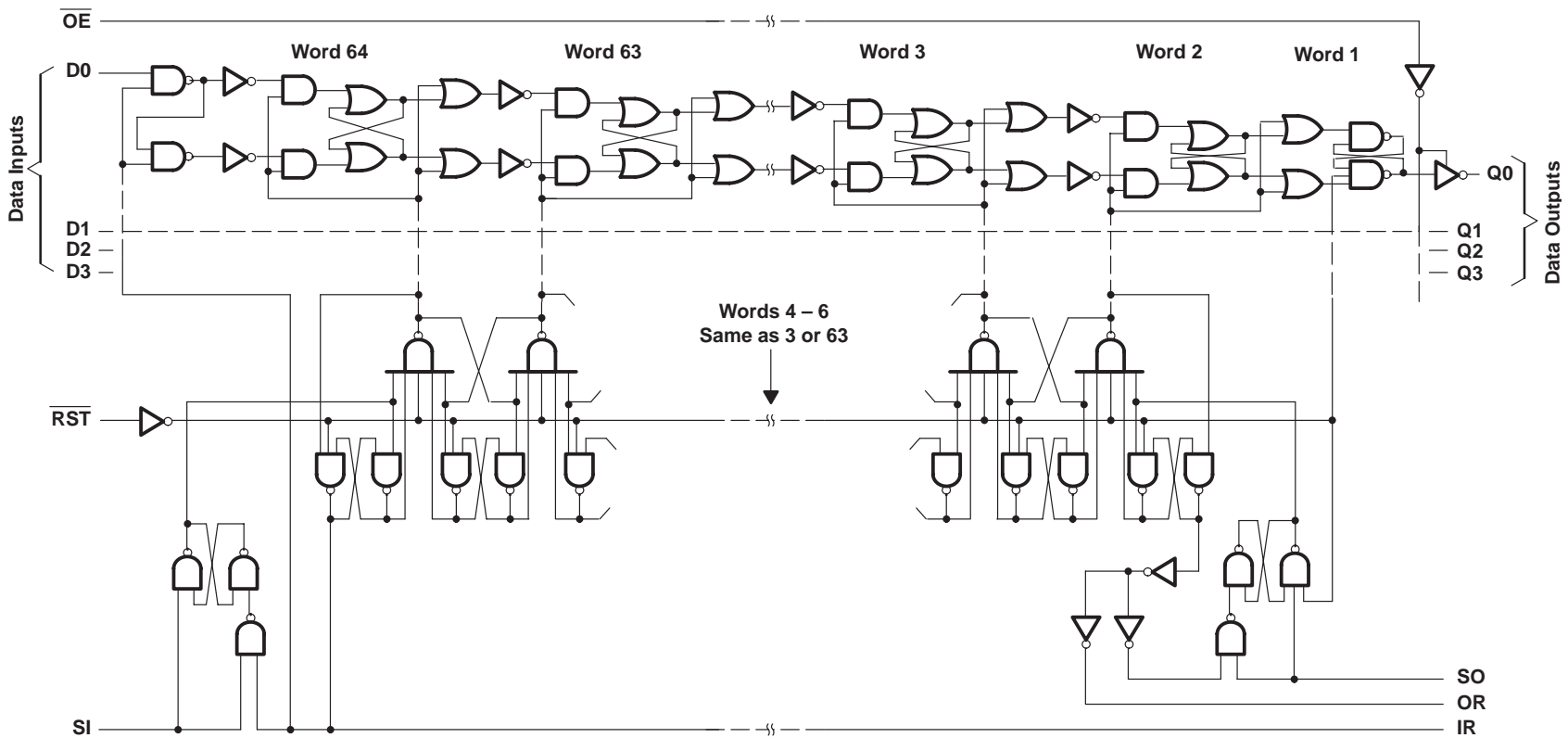


Pin numbers shown are for the DW and N packages.

SN74ALS234
64 × 4 ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY

SDAS106B – OCTOBER 1986 – REVISED SEPTEMBER 1993

logic diagram (positive logic)

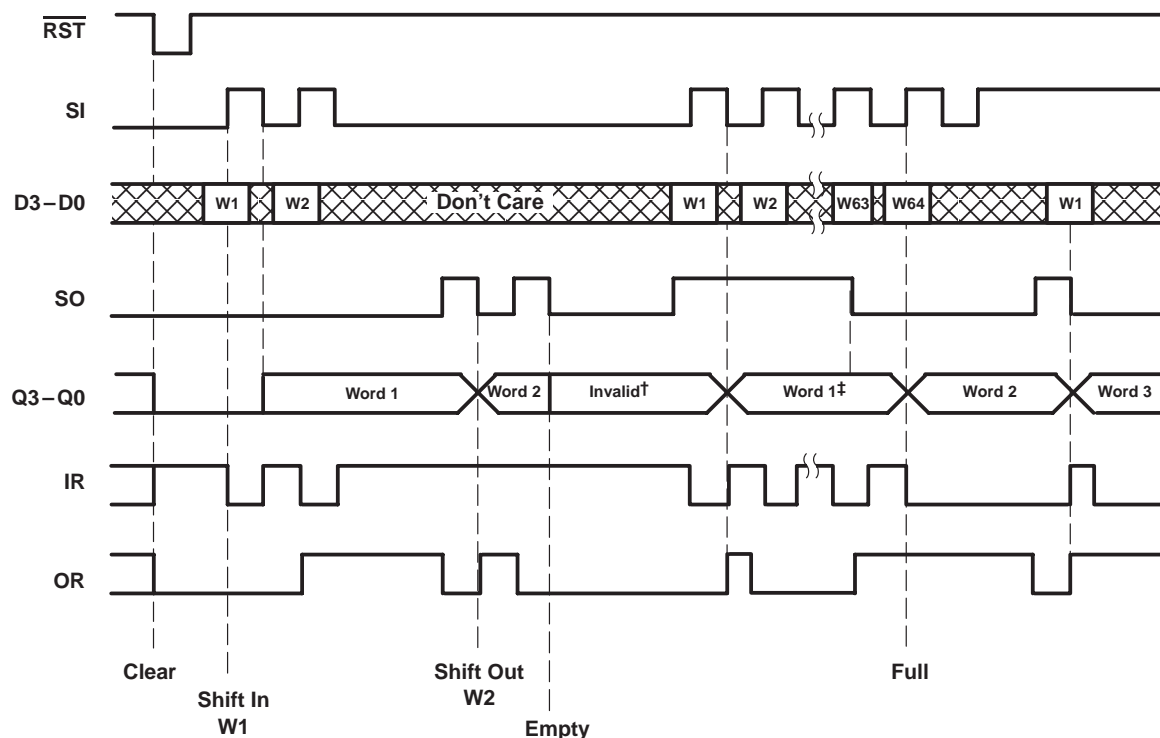


SN74ALS234

64 × 4 ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY

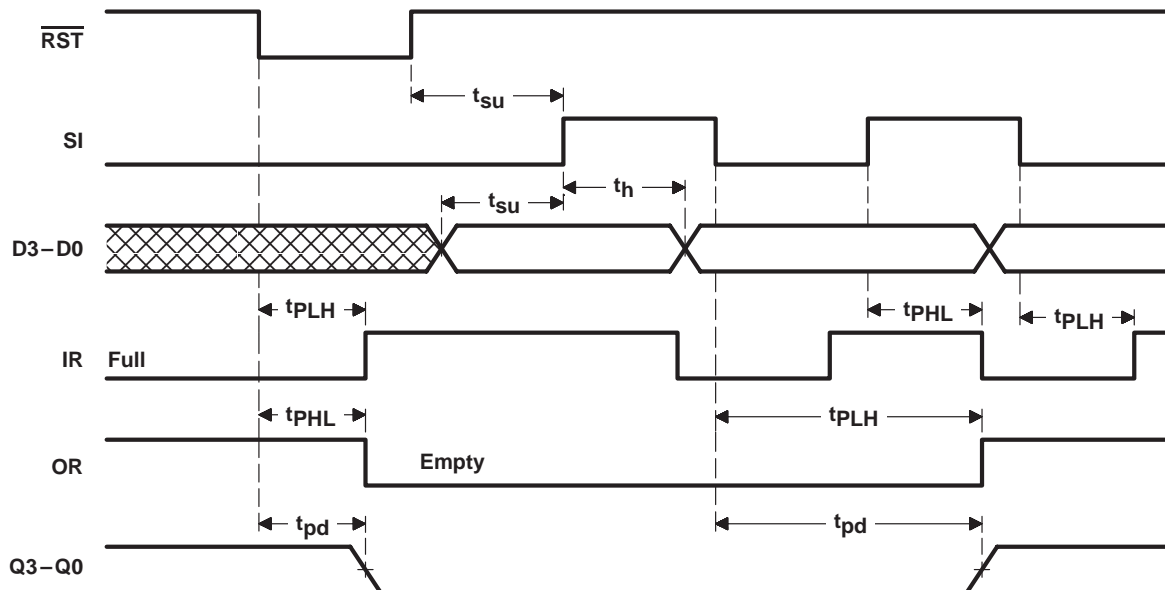
SDAS106B – OCTOBER 1986 – REVISED SEPTEMBER 1993

timing diagram



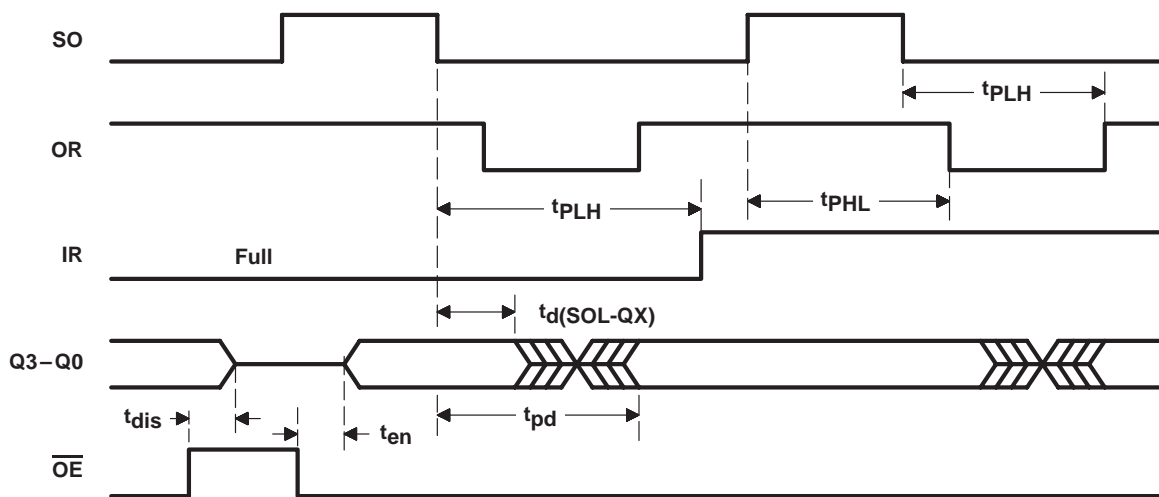
† The last data word shifted out of the FIFO remains at the output until a new word falls through or a $\overline{\text{RST}}$ pulse clears the FIFO.

‡ While the output data is considered valid only when the OR flag is high, the stored data remains at the outputs. Any additional words written into the FIFO will stack up behind the first word and will not appear at the output until SO is taken low.



NOTE: SO is low.

Figure 1. Master Reset and Data-In Waveforms



NOTE: SI is low.

Figure 2. Data-Out Waveforms

SN74ALS234

64 × 4 ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY

SDAS106B – OCTOBER 1986 – REVISED SEPTEMBER 1993

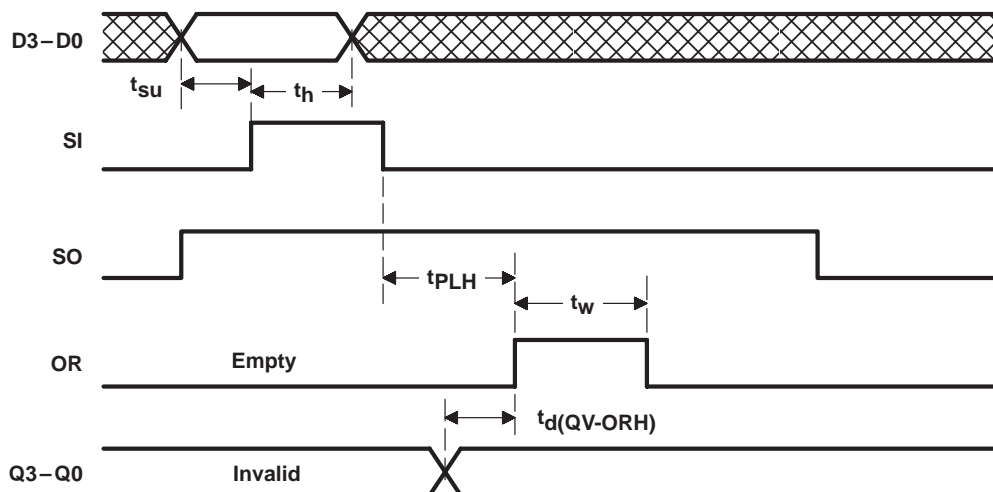


Figure 3. Data Fall-Through Waveforms

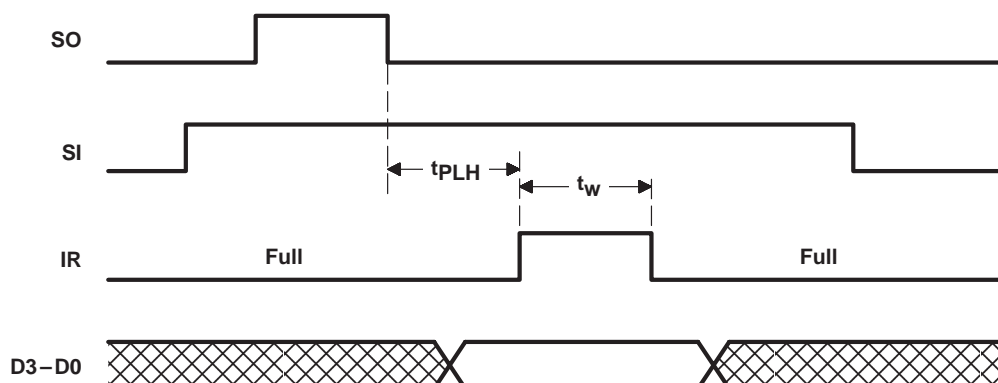


Figure 4. Automatic Data-In Waveforms

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V_{CC} (see Note 1)	7 V
Input voltage, V_I	7 V
Voltage applied to a disabled 3-state output	5.5 V
Operating free-air temperature range, T_A	0°C to 70°C
Storage temperature range	-65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to GND.

SN74ALS234

64 × 4 ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY

SDAS106B – OCTOBER 1986 – REVISED SEPTEMBER 1993

recommended operating conditions

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		4.5	5	5.5	V
V _{IH}	High-level input voltage		2			V
V _{IL}	Low-level input voltage				0.8	V
I _{OH}	High-level output current	Q outputs			– 2.6	mA
		IR and OR			– 0.4	
I _{OL}	Low-level output current	Q outputs			24	mA
		IR and OR			8	
f _{clock}	Clock frequency	SI or SO	0		30	MHz
t _w	Pulse duration	SI or SO	High or low	15		ns
		RST	Low	15		
t _{su}	Setup time before SI↑	Data		0		ns
		RST	High (inactive)	15		
t _h	Hold time, data after SI↑		17			ns
T _A	Operating free-air temperature		0		70	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
V _{IK}		V _{CC} = 4.5 V,	I _I = –18 mA			–1.2	V
V _{OH}	Any Q	V _{CC} = 4.5 V	I _{OH} = –1 mA				V
			I _{OH} = –2.6 mA	2.4	3.2		
	IR, OR	V _{CC} = 4.5 V,	I _{OH} = –0.4 mA	2.7	3.4		
V _{OL}	Any Q	V _{CC} = 4.5 V	I _{OL} = 12 mA		0.25	0.4	V
			I _{OL} = 24 mA		0.35	0.5	
	IR, OR	V _{CC} = 4.5 V	I _{OL} = 4 mA		0.25	0.4	
			I _{OL} = 8 mA		0.35	0.5	
I _{OZH}		V _{CC} = 5.5 V,	V _O = 2.7 V			20	μA
I _{OZL}		V _{CC} = 5.5 V,	V _O = 0.4 V			–20	μA
I _I		V _{CC} = 5.5 V,	V _I = 7 V			0.1	mA
I _{IH}		V _{CC} = 5.5 V,	V _I = 2.7 V			20	μA
I _{IL}		V _{CC} = 5.5 V,	V _I = 0.4 V			–0.1	mA
I _{O‡}		V _{CC} = 5.5 V,	V _O = 2.25 V	–30		–112	mA
I _{CC}		V _{CC} = 5.5 V	Low		100	145	mA
			High		97	142	
			Disabled		103	148	

† All typical values are at V_{CC} = 5 V, T_A = 25°C.

‡ The output conditions have been chosen to produce a current that closely approximates one half of the true short-circuit output current, I_{OS}.

SN74ALS234

64 × 4 ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY

SDAS106B – OCTOBER 1986 – REVISED SEPTEMBER 1993

switching characteristics (see Figure 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 5 V, C _L = 50 pF, R1 = 500 Ω, R2 = 500 Ω, T _A = 25°C			V _{CC} = 4.5 V to 5.5 V, C _L = 50 pF, R1 = 500 Ω, R2 = 500 Ω, T _A = MIN to MAX†		UNIT
			MIN	TYP	MAX	MIN	MAX	
f _{max}	SI		35			30		MHz
	SO		35			30		
tw [‡]	IR high		15			8		ns
tw [§]	OR high		19			8		ns
t _d (QV-ORH)	Q valid before OR↑		6 9			−5 12		ns
t _d (SOL-QX)	Q valid after SO↓		13			4		ns
t _{pd}	SI↓	Q	600 800			350 1000		ns
t _{PHL}	SI↑	IR	20 26			8 30		ns
t _{PLH}	SI↓		16 21			6 25		
t _{PLH} [¶]	SI↓	OR	600 800			350 1000		ns
t _{pd}	SO↓	Q	13 17			4 22		ns
t _{PHL}	SO↑	OR	23 27			7 33		ns
t _{PLH}	SO↓		20 24			6 30		
t _{PLH} [¶]	SO↓	IR	600 800			350 1000		ns
t _{PHL}	RST↓	OR	22 26			10 34		ns
t _{PLH}		IR	17 21			6 27		
t _{PHL}	$\overline{\text{RST}}$ ↓	Q	14 17			5 19		ns
t _{dis}	$\overline{\text{OE}}$ ↑	Q	7 13			2 15		ns
t _{en}	$\overline{\text{OE}}$ ↓	Q	6 12			2 13		ns

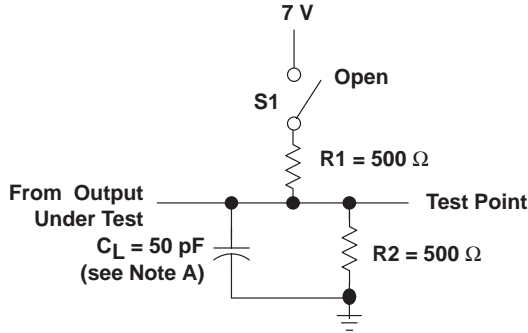
† For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

‡ The IR output pulse occurs when the FIFO is full, SI is high, and SO is pulsed (see Figure 4).

§ The OR output pulse occurs when the FIFO is empty, SO is high, and SI is pulsed (see Figure 3).

¶ Data throughput or fall-through times

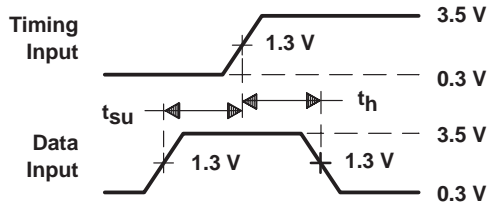
PARAMETER MEASUREMENT INFORMATION



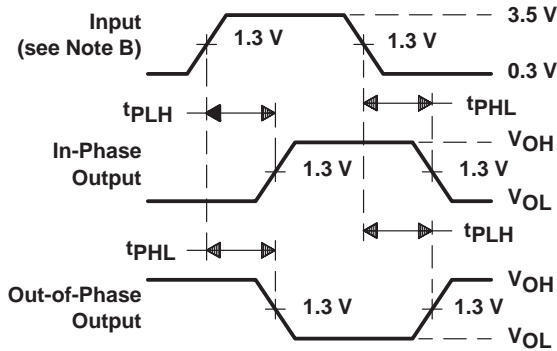
SWITCH POSITION TABLE

TEST	S1
t_{PLH}	Open
t_{PHL}	Open
t_{PZH}	Open
t_{PZL}	Closed
t_{PHZ}	Open
t_{PLZ}	Closed

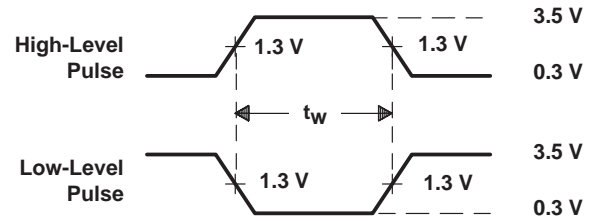
LOAD CIRCUIT FOR 3-STATE OUTPUTS



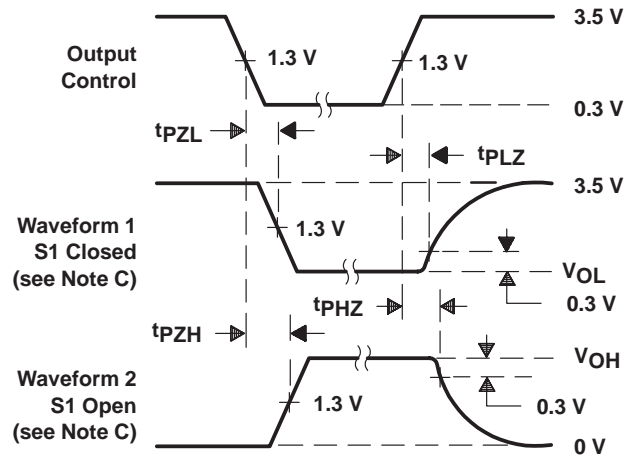
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES, 3-STATE OUTPUTS

- NOTES: A. C_L includes probe and jig capacitance.
 B. All input pulses are supplied by generators having the following characteristics: $PRR \leq 1 \text{ MHz}$, $Z_0 = 50 \Omega$, $t_r \leq 2 \text{ ns}$, $t_f \leq 2 \text{ ns}$.
 C. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 D. The outputs are measured one at a time with one transition per measurement.

Figure 5. Load Circuit and Voltage Waveforms

SN74ALS234

64 × 4 ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY

SDAS106B – OCTOBER 1986 – REVISED SEPTEMBER 1993

APPLICATION INFORMATION

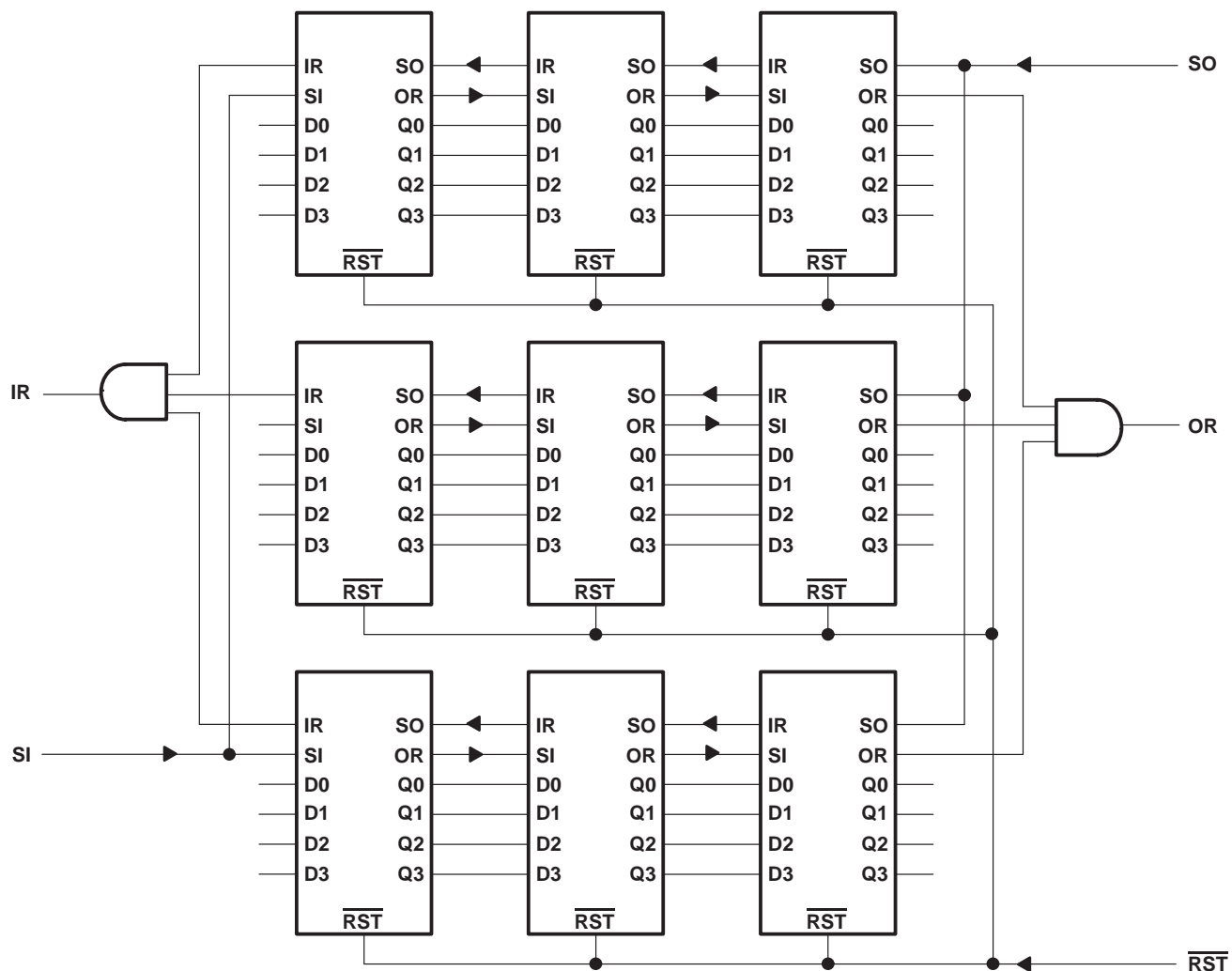


Figure 6. 192-Word by 12-Bit Expansion

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.